

L Number	Hits	Search Text	DB	Time stamp
1	1	("5120672").PN.	USPAT	2004/04/07 15:57
2	1	((("5120672").PN.) and (non or volatile or semiconductor or memory or device or charge or storage or region or substrate or top or portion or conductive or side or wall or control or gate or floating or source or drain or electrode or side or insulative or insulating or underlying or spacer or mask or width or substantially or height or equal or lower or than or shape or unit or cell or LDD or dilectric or ONO or electrical or electrically or bit or line or select or selected or isolated or isolate or poly or inter)	USPAT	2004/04/07 16:07
3	1	("4851365").PN.	USPAT	2004/04/07 16:07
4	1	((("4851365").PN.) and (non or volatile or semiconductor or memory or device or charge or storage or region or substrate or top or portion or conductive or side or wall or control or gate or floating or source or drain or electrode or side or insulative or insulating or underlying or spacer or mask or width or substantially or height or equal or lower or than or shape or unit or cell or LDD or dilectric or ONO or electrical or electrically or bit or line or select or selected or isolated or isolate or poly or inter)	USPAT	2004/04/07 16:34
5	1	("5073513").PN.	USPAT	2004/04/07 16:34
6	1	((("5073513").PN.) and (non or volatile or semiconductor or memory or device or charge or storage or region or substrate or top or portion or conductive or side or wall or control or gate or floating or source or drain or electrode or side or insulative or insulating or underlying or spacer or mask or width or substantially or height or equal or lower or than or shape or unit or cell or LDD or dilectric or ONO or electrical or electrically or bit or line or select or selected or isolated or isolate or poly or inter)	USPAT	2004/04/07 16:35
7	1	("4852062").PN.	USPAT	2004/04/07 16:35
8	1	((("4852062").PN.) and (non or volatile or semiconductor or memory or device or charge or storage or region or substrate or top or portion or conductive or side or wall or control or gate or floating or source or drain or electrode or side or insulative or insulating or underlying or spacer or mask or width or substantially or height or equal or lower or than or shape or unit or cell or LDD or dilectric or ONO or electrical or electrically or bit or line or select or selected or isolated or isolate or poly or inter)	USPAT	2004/04/07 16:38
9	1	("6291297").PN.	USPAT	2004/04/07 16:38
10	1	((("6291297").PN.) and (non or volatile or semiconductor or memory or device or charge or storage or region or substrate or top or portion or conductive or side or wall or control or gate or floating or source or drain or electrode or side or insulative or insulating or underlying or spacer or mask or width or substantially or height or equal or lower or than or shape or unit or cell or LDD or dilectric or ONO or electrical or electrically or bit or line or select or selected or isolated or isolate or poly or inter)	USPAT	2004/04/07 16:44
11	1	("6583009").PN.	USPAT	2004/04/07 16:44
12	1	((("6583009").PN.) and (non or volatile or semiconductor or memory or device or charge or storage or region or substrate or top or portion or conductive or side or wall or control or gate or floating or source or drain or electrode or side or insulative or insulating or underlying or spacer or mask or width or substantially or height or equal or lower or than or shape or unit or cell or LDD or dilectric or ONO or electrical or electrically or bit or line or select or selected or isolated or isolate or poly or inter)	USPAT	2004/04/07 16:48
13	1	("5498558").PN.	USPAT	2004/04/07 16:48

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14	1	((("5498558").PN.) and (non or volatile or semiconductor or memory or device or charge or storage or region or substrate or top or portion or conductive or side or wall or control or gate or floating or source or drain or electrode or side or insulative or insulating or underlying or spacer or mask or width or substantially or height or equal or lower or than or shape or unit or cell or LDD or dilectric or ONO or electrical or electrically or bit or line or select or selected or isolated or isolate or poly or inter)	USPAT	2004/04/07 16:49
15	3141	257/296	USPAT	2004/04/07 16:49
16	1267	257/314	USPAT	2004/04/07 16:49
17	2248	257/315	USPAT	2004/04/07 16:49
18	2534	257/316	USPAT	2004/04/07 16:50
19	570	257/319	USPAT	2004/04/07 16:50
20	1341	257/336	USPAT	2004/04/07 16:50
21	413	257/334	USPAT	2004/04/07 16:50
22	1573	257/344	USPAT	2004/04/07 16:50
23	1459	257/408	USPAT	2004/04/07 16:50
24	476	257/311	USPAT	2004/04/07 16:50
25	486	257/318	USPAT	2004/04/07 16:50
26	525	257/320	USPAT	2004/04/07 16:51
27	134	257/549	USPAT	2004/04/07 16:51
28	105	257/550	USPAT	2004/04/07 16:51

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